TOSHIBA 1SV231

TOSHIBA VARIABLE CAPACITANCE DIODE SILICON EPITAXIAL PLANAR TYPE

1 S V 2 3 1

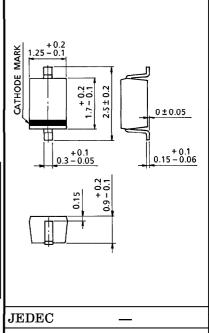
CATV TUNING

Unit in mm

- High Capacitance Ratio : $C_{2V}/C_{25V}=15$ (Typ.)
- Excellent C-V Characteristics, and Small Tracking Error.
- Useful for Small Size Tuner.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Reverse Voltage	v_{R}	30	V
Peak Reverse Voltage V _{RM}		$(R_L = 10 \mathrm{k}\Omega)$	V
Junction Temperature	T_{j}	125	°C
Storage Temperature Range	$\mathrm{T_{stg}}$	-55~125	°C



JEDEC	_	
EIAJ	_	
TOSHIBA	1-1E1A	

Weight: 0.004g

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

	<u> </u>					
CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Reverse Voltage	v_{R}	$I_R = 1 \mu A$	30	_	_	V
Reverse Current	$I_{\mathbf{R}}$	$V_R = 28V$	_	_	10	nA
Capacitance	c_{2V}	$V_R=2V, f=1MHz$	41.0	45.0	49.5	рF
Capacitance	C_{25V}	V_R =25V, f=1MHz	2.7	3.0	3.4	рF
Capacitance Ratio	C_{2V}/C_{25V}	_	14	15	_	_
Series Resistance	$r_{\rm S}$	$V_R=5V$, $f=470MHz$	_	1.05	1.25	Ω

(Note 1): Available in matched group for capacitance to 2.5%.

$$\frac{\text{C (Max.)} - \text{C (Min.)}}{\text{C (Min.)}} \leq 0.025$$
$$(\text{V}_{\text{R}} = 2 \sim 25\text{V})$$





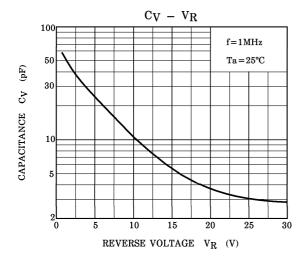
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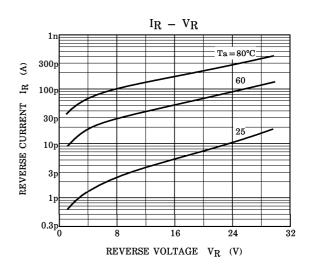
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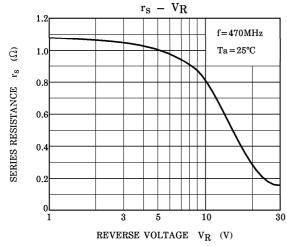
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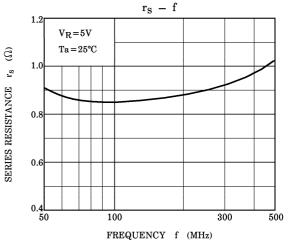
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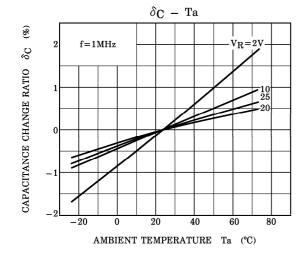
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NOTE :
$$\delta_{\text{C}}$$
 (%) = $\frac{\text{C (Ta)} - \text{C (25)}}{\text{C (25)}} \times 100$

SPICE PARAMETER

SPICE MODEL : BERKLEY SPICE.2G.6 DIODE MODEL

DATA FORMAT : MODEL FORMAT

SPICE SYMBOL : $I_S(A)$, $R_S(\Omega)$, N(-), CJ0(F), $V_J(V)$, M(-), $B_V(V)$, $I_{BV}(A)$

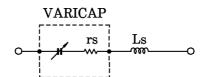
FREQUENCY RANGE : $f = 0.1 \sim 3 \text{ GHz}$

REVERSE VOLTAGE RANGE : $V_R = 2 \sim 25 \text{ V}$

AMBIENT TEMPERATURE : $Ta = 27^{\circ}C$

PARAMETER

$$\begin{array}{rcl} I_S & = & 1.195E - 14 \\ N & = & & 1.072 \\ B_V & = & & 30 \\ I_{BV} & = & 1.00E - 04 \\ R_S & = & & 1.05 \\ CJ0 & = & 9.127E - 11 \\ V_J & = & 5.096 \\ M & = & 2.031 \\ \hline L_S & = & 1.00E - 09 \\ \end{array}$$



(Note 1): These parameters from IS to M mean die characteristic.

Actually device has lead inductance so Ls is necessary for simulation.

And please use default value except above parameters.

(Note 2): R_S shows the value at the condition of $V_R = 5\,V$ and $f = 470\,MHz$. If another value is needed, please refer to $R_S - V_R$ curve in this data sheets.